

November 1999 ADVANCE INFORMATION

FDC602P

P-Channel 2.5V Specified PowerTrench® MOSFET

General Description

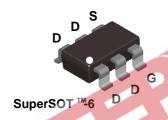
This P-Channel 2.5V specified MOSFET uses a rugged gate version of Fairchild's advanced PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V – 12V).

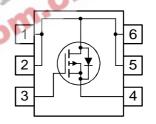
Applications

- Battery management
- Load switch
- Battery protection

Features

- -5.5 A, -12 V $R_{DS(ON)} = 0.033~\Omega~@~V_{GS} = -4.5~V$ $R_{DS(ON)} = 0.052~\Omega~@~V_{GS} = -2.5~V$
- Fast switching speed.
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS(ON)}}$.





Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-12	V
V _{GSS}	Gate-Source Voltage		±12	V
I _D	Drain Current - Continuous	(Note 1a)	-5.5	Α
	– Pulsed		-30	
P _D	Maximum Power Dissipation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
T_J , T_{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

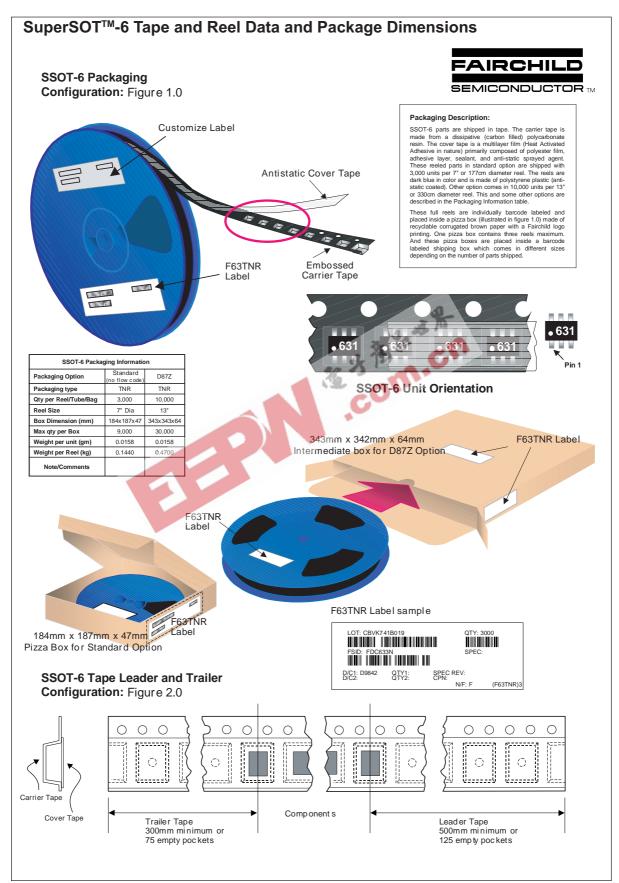
Package Marking and Ordering Information

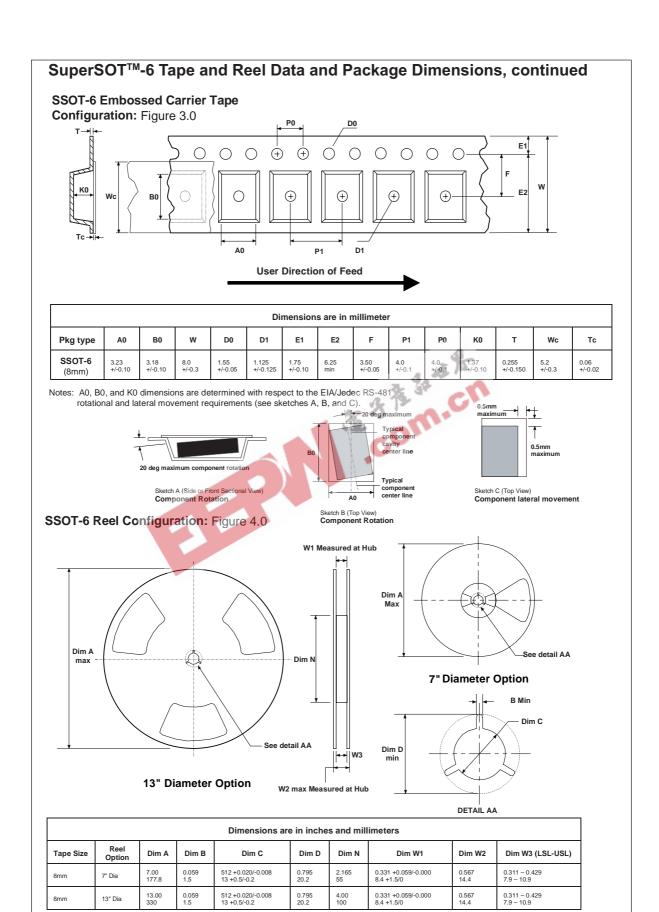
Device Marking	Device	Reel Size	Tape width	Quantity
.602	FDC602P	7"	8mm	3000 units

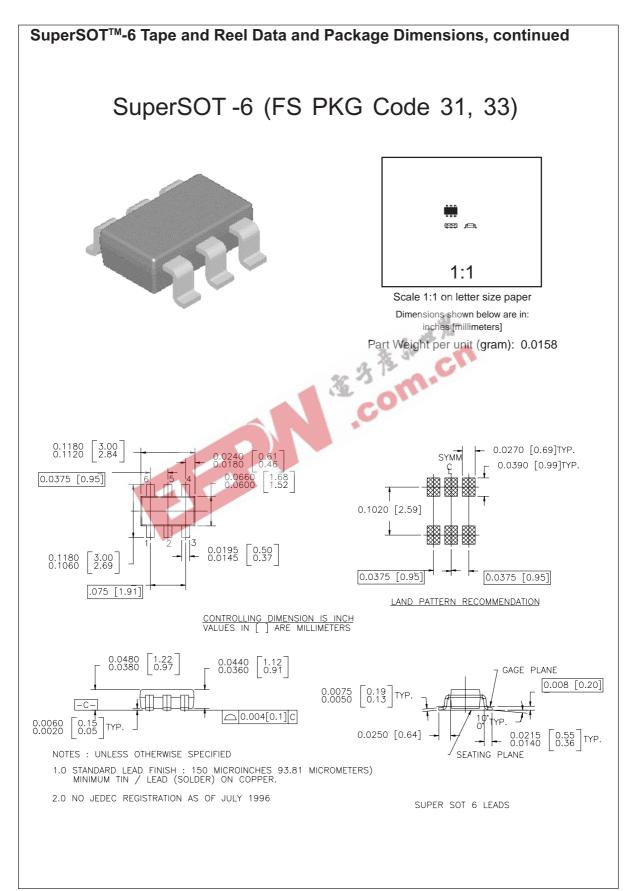
Electri	Electrical Characteristics T _A = 25°C unless otherwise noted						
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Off Char	Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-12			V	
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ	
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 12 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA	
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -12 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA	
On Char	On Characteristics (Note 2)						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.6		-1.5	V	
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = -4.5 \text{ V}, I_{D} = -5.5 \text{ A} $ $V_{GS} = -2.5 \text{ V}, I_{D} = -4.4 \text{ A}$			0.033 0.052	Ω	
Drain-S	ource Diode Characteristics a	and Maximum Ratings	•				
Is	Maximum Continuous Drain-Source Diode Forward Current -1.3 A			Α			
V_{SD}	Drain-Source Diode Forward	$V_{GS} = 0 \text{ V}, I_{S} = -1.3 \text{ A (Note 2)}$			-1.2	V	

- Notes:
 1. R_{θJA} is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design while R_{θCA} is determined by the user's board design.
 a. 78°C/W when mounted on a 1in² pad of 2oz copper on FR-4 board.
 b. 156°C/W when mounted on a minimum pad.
 2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

Voltage









TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

 $\begin{array}{lll} E^2 CMOS^{TM} & Power Trench^{\circledR} \\ FACT^{TM} & QFET^{TM} \\ FACT \ Quiet \ Series^{TM} & QS^{TM} \end{array}$

 $\begin{array}{lll} {\sf FAST}^{\circledcirc} & {\sf Quiet\ Series^{\sf TM}} \\ {\sf FASTr^{\sf TM}} & {\sf SuperSOT^{\sf TM}\text{--}3} \\ {\sf GTO^{\sf TM}} & {\sf SuperSOT^{\sf TM}\text{--}6} \\ {\sf HiSeC^{\sf TM}} & {\sf SuperSOT^{\sf TM}\text{--}8} \end{array}$

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

 A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed Full Production		This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.